

Supporting Information

The Behavior of *E. Coli* with Variable Surface Morphology Changes on Charged Semiconductor Interfaces

Divya Iyer, ‡ Alexey V. Gulyuk, † Pramod Reddy, & Ronny Kirste, & Ramon Collazo, † Dennis R. LaJeunesse, ‡
Albena Ivanisevic†**

†Department of Materials Science and Engineering, North Carolina State University, Raleigh, North Carolina, 27695, USA

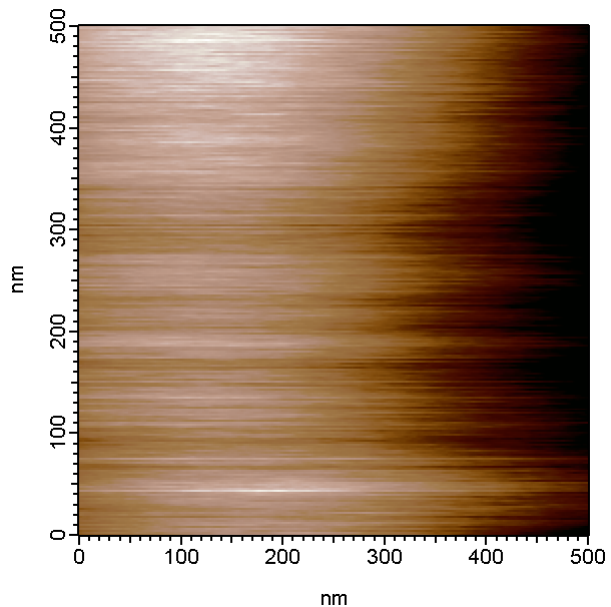
‡ Department of Nanoscience, Joint School of Nanoscience and Nanoengineering, University of North Carolina-Greensboro, Greensboro, North Carolina, 27401, USA

& Adroit Materials, 2054 Kildaire Farm Rd., Suite 205, Cary, North Carolina 27518, USA

*authors to whom correspondence should be addressed: drlajeun@uncg.edu, ivanisevic@ncsu.edu

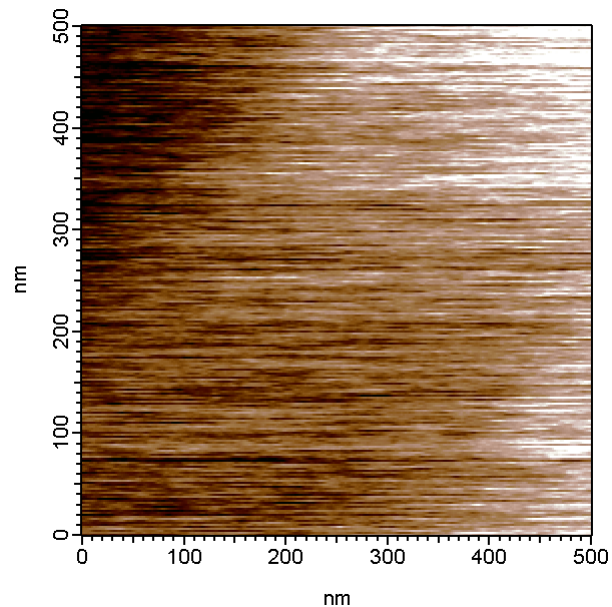
Figure S1. Representative KPFM scans of GaN samples under three conditions: no UV, UV on, UV off.

No UV



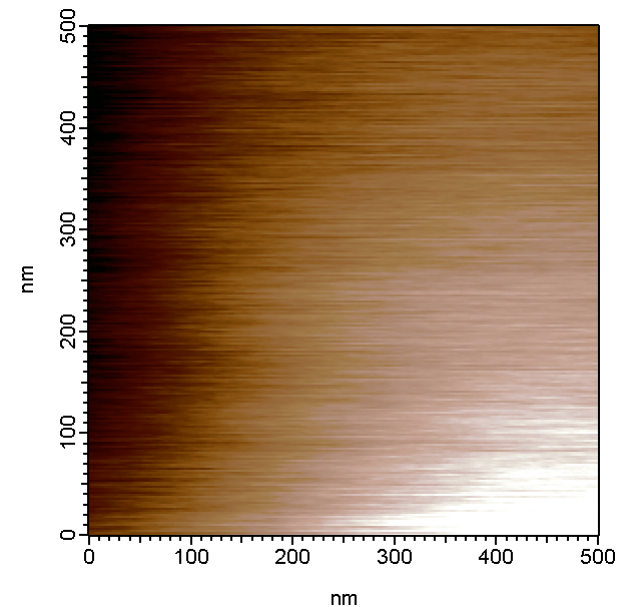
RMS charge:
247.458 mV

UV on



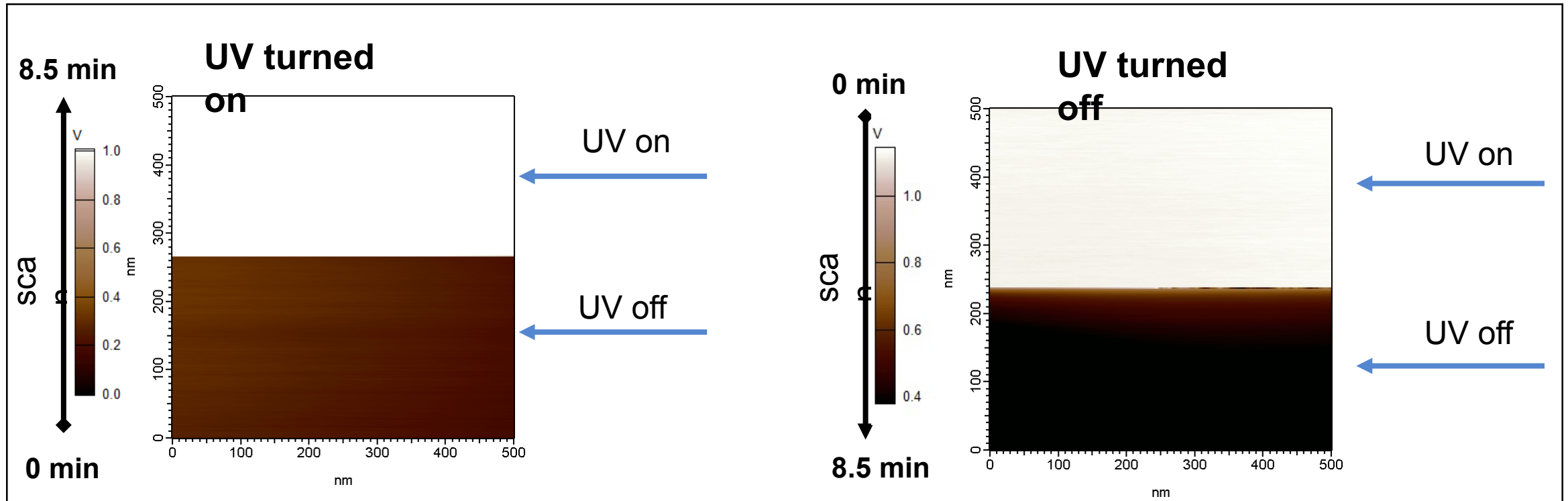
RMS charge:
1.132 V

UV off



RMS charge:
186.305 mV

Figure S2. Representative KPFM scans of GaN in the intermediate conditions – transferring from uncharged to charged and from charged to uncharged state.



RMS charge:
798.809 mV

RMS charge:
855.125 mV